

2SC2238 2SC2238A 2SC2238B

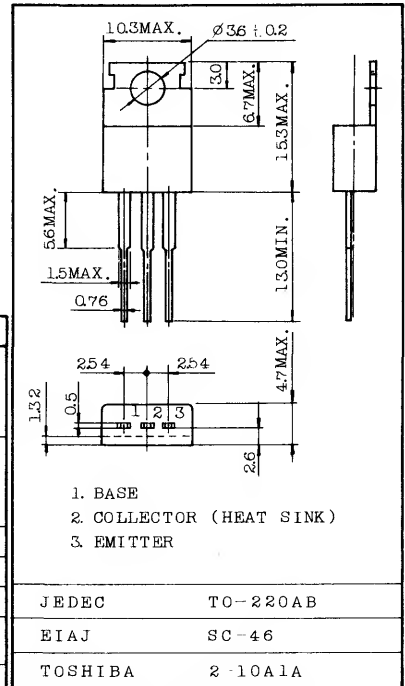
SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

POWER AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATIONS.

FEATURES:

- High Transition Frequency : $f_T=100\text{MHz}$ (Typ.)
- Complementary to 2SA968, 2SA968A, and 2SA968B.

Unit in mm



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	2SC2238	V _{CB0}	160	V
	2SC2238A		180	
	2SC2238B		200	
Collector-Emitter Voltage	2SC2238	V _{CEO}	160	V
	2SC2238A		180	
	2SC2238B		200	
Emitter-Base Voltage		V _{EBO}	5	V
Collector Current		I _C	1.5	A
Emitter Current		I _E	-1.5	A
Collector Power Dissipation (Tc=25°C)		P _C	25	W
Junction Temperature		T _j	150	°C
Storage Temperature Range		T _{stg}	-55~150	°C

JEDEC TO-220AB
EIAJ SC-46
TOSHIBA 2-10A1A
Mounting Kit No. AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CB0}	V _{CB} =160V, I _E =0	-	-	1.0	μA
Emitter Cut-off Current		I _{EBO}	V _{EB} =5V, I _C =0	-	-	1.0	μA
Collector-Emitter Breakdown Voltage	2SC2238	V _{(BR)CEO}	I _C =10mA, I _B =0	160	-	-	V
	2SC2238A			180	-	-	
	2SC2238B			200	-	-	
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	I _E =1mA, I _C =0	5	-	-	V
DC Current Gain		h _{FE} (Note)	V _{CE} =5V, I _C =100mA	70	-	240	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =500mA, I _B =50mA	-	-	1.5	V
Base-Emitter Voltage		V _{BE}	V _{CE} =5V, I _C =500mA	-	-	1.0	V
Transition Frequency		f _T	V _{CE} =10V, I _C =100mA	-	100	-	MHz
Collector Output Capacitance		C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	25	-	pF

Note : h_{FE} Classification 0 : 70~140, Y : 120~240

2SC2238 · 2SC2238A · 2SC2238B

